



First Named Inventor	Michael Smith	INFORMATION DISCLOSURE STATEMENT FORM PTO-1449
Serial No.	10/656,636	
Filing Date	September 5, 2003	
Group Art Unit	2811	
Examiner Name	Unknown	
Confirmation No.	8125	
Attorney Docket No.	400.245US01	
Title: TRENCH CORNER EFFECT BIDIRECTIONAL FLASH MEMORY CELL		Sheet 1 of 7

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